VS-6EWH06FN-M3

Vishay Semiconductors

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RoHS

COMPLIANT HALOGEN

FREE

Hyperfast Rectifier, 6 A FRED Pt[®]



PRIMARY CHARACTERISTICS									
I _{F(AV)}	6 A								
V _R	600 V								
V _F at I _F	1.26 V								
t _{rr} (typ.)	18 ns								
T _J max.	175 °C								
Package	DPAK (TO-252AA)								
Circuit configuration	Single								

FEATURES

- Hyperfast recovery time, reduced Qrr and soft recovery
- 175 °C maximum operating junction temperature
- For PFC CRM/CCM operation
- Low forward voltage drop
- Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS										
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS						
Peak repetitive reverse voltage	V _{RRM}		600	V						
Average rectified forward current	I _{F(AV)}	T _C = 144 °C	6							
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	70	А						
Peak repetitive forward current	I _{FM}	$T_{C} = 144 \ ^{\circ}C, f = 20 \ kHz, d = 50 \ \%$	12							
Operating junction and storage temperatures	T _J , T _{Stg}		-65 to +175	°C						

ELECTRICAL SPECIFICATIONS (T _J = 25 $^{\circ}$ C unless otherwise specified)									
PARAMETER	TER SYMBOL TEST CONDITIONS								
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-				
Forward voltage	V _F	$I_F = 6 A$	-	1.60	2.1	V			
		I _F = 6 A, T _J = 150 °C	-	1.26	1.7				
Povereo lookago ourrent	I _R	$V_{R} = V_{R}$ rated	-	-	50				
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	-	250	μA			
Junction capacitance	CT	V _R = 600 V		3.5	-	pF			
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nH			

Revision: 12-Apr-18

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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 $^{\circ}$ C unless otherwise specified)										
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1 \text{ A}, dI_F/dt = 10$	-	18	25					
	t _{rr}	$I_F = 1 \text{ A}, dI_F/dt = 50$	-	22	-					
		T _J = 25 °C		-	27	-	ns			
		T _J = 125 °C	I _F = 6 A dI _F /dt = 200 A/μs	-	37	-				
Dook rooovony ourront	I _{RRM}	T _J = 25 °C		-	4.1	-	А			
Peak recovery current		T _J = 125 °C	$V_{\rm B} = 390 \text{ V}$	-	5.3	-	~			
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	57	-	nC			
		T _J = 125 °C		_	103	-	nc			

THERMAL - MECHANICAL SPECIFICATIONS										
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS				
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C				
Thermal resistance, junction to case per leg	R _{thJC}		-	-	3	°C/W				
Approximate weight				0.3		g				
Approximate weight				0.01		oz.				
Marking device		Case style DPAK (TO-252AA)	6EWH06FN							

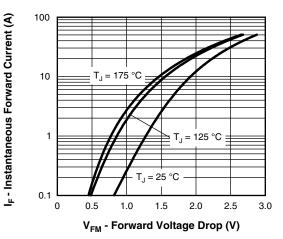
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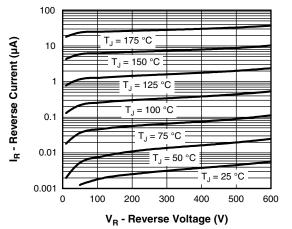
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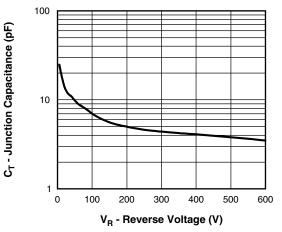
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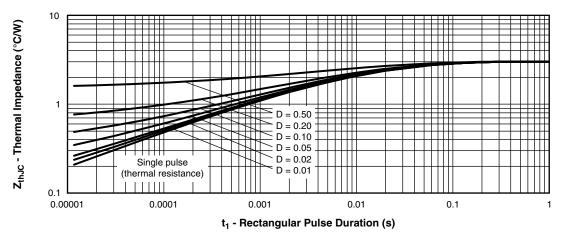
Fig. 1 - Typical Forward Voltage Drop Characteristics









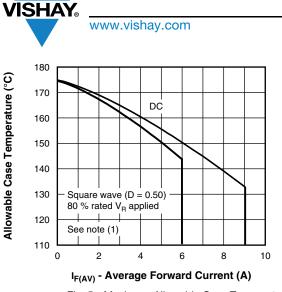


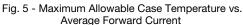


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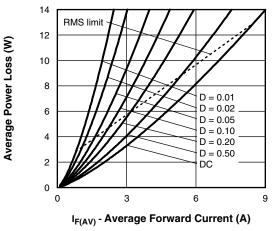


Fig. 6 - Forward Power Loss Characteristics

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$; $Pd = forward power loss = I_{F(AV)} \times V_{FM} at (I_{F(AV)}/D)$ (see fig. 6); $Pd_{REV} = inverse power loss = V_{R1} \times I_R (1 - D)$; $I_R at V_{R1} = rated V_R$

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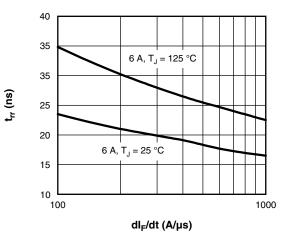


Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt

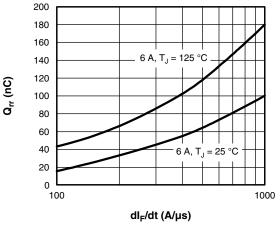


Fig. 8 - Typical Stored Charge vs. dI_F/dt

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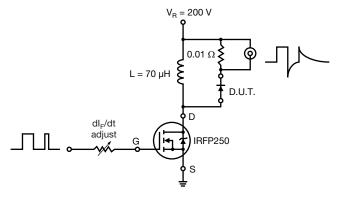


Fig. 9 - Reverse Recovery Parameter Test Circuit

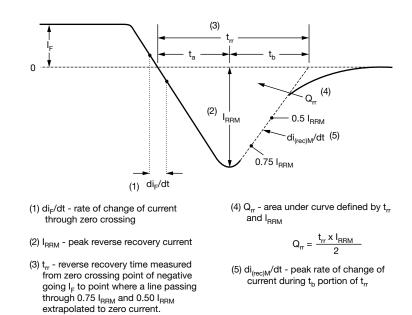


Fig. 10 - Reverse Recovery Waveform and Definitions

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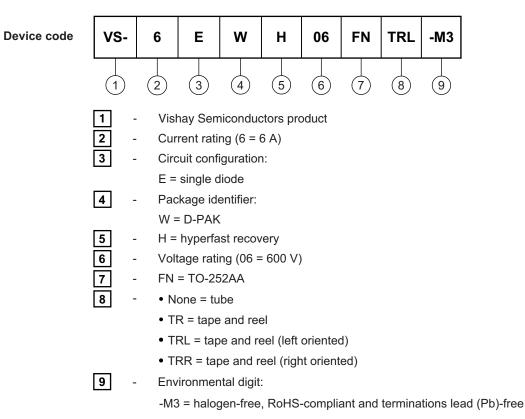
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ORDERING INFORMATION TABLE

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ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-6EWH06FN-M3	75	3000	Antistatic plastic tube							
VS-6EWH06FNTR-M3	2000	2000	13" diameter reel							
VS-6EWH06FNTRL-M3	3000	3000	13" diameter reel							
VS-6EWH06FNTRR-M3	3000	3000	13" diameter reel							

LINKS TO RELATED DOCUMENTS							
Dimensions	www.vishay.com/doc?95627						
Part marking information	www.vishay.com/doc?95176						
Packaging information	www.vishay.com/doc?95033						
SPICE model	www.vishay.com/doc?95187						

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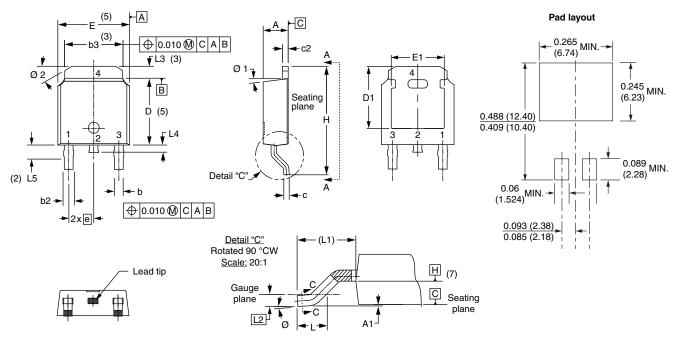


Outline Dimensions

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D-PAK (TO-252AA) "M"

DIMENSIONS in millimeters and inches



SYMBOL	MILLIN	IETERS	INC	HES	NOTES	NOTES	SYMBOL		MILLIMETERS		INCHES	
STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STINDUL	MIN.	MAX.	MIN.	MAX.	NOTES
А	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090	BSC	
A1	-	0.13	-	0.005			Н	9.40	10.41	0.370	0.410	
b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.070	
b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	BREF.	
b3	4.95	5.46	0.195	0.215	3		L2	0.51 BSC		0.020 BSC		
С	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.050	3
c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.040	
D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.060	2
D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°	
E	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°	
E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°	
NI - I												

Notes

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Lead dimension uncontrolled in L5

⁽³⁾ Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad

(4) Section C - C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip

(5) Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

- (6) Dimension b1 and c1 applied to base metal only
- ⁽⁷⁾ Datum A and B to be determined at datum plane H
- ⁽⁸⁾ Outline conforms to JEDEC[®] outline TO-252AA

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